(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
4 March 2004 (04.03.2004)

PCT

(10) International Publication Number
WO 2004/019394 A1

(51) International Patent Classification[7]: H01L 21/28, 29/49, 21/8234, 21/8238

(21) International Application Number: PCT/US2003/026487

(22) International Filing Date: 21 August 2003 (21.08.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/225,605 22 August 2002 (22.08.2002) US

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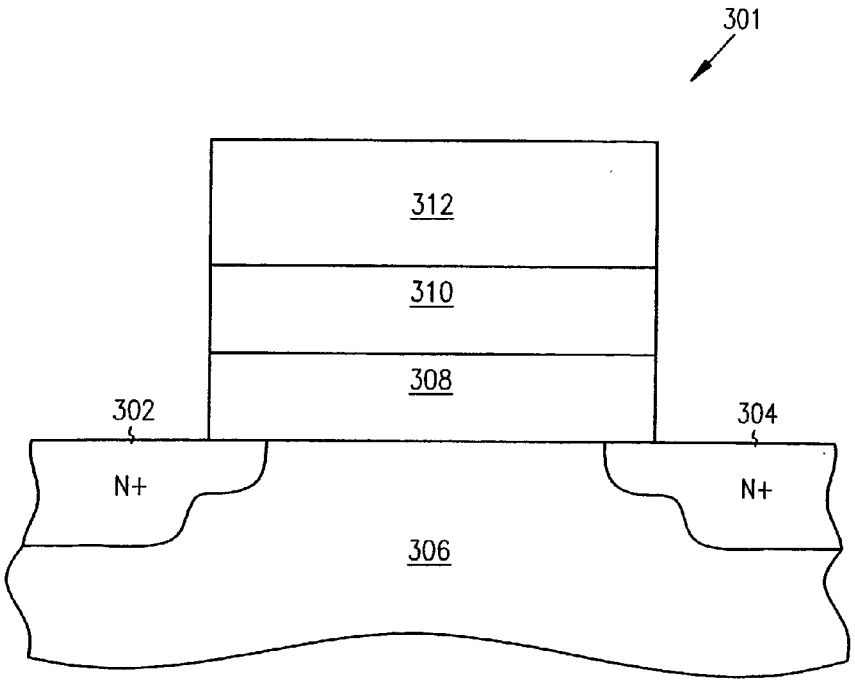
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

[Continued on next page]

(54) Title: ATOMIC LAYER DEPOSITION OF CMOS GATES



(57) Abstract: Structures, systems and methods for transistors having gates with variable work functions formed by atomic layer deposition are provided. One transistor embodiment includes a first source/drain region, a second source/drain region, and a channel region therebetween. A gate is separated from the channel region by a gate insulator. The gate includes a ternary metallic conductor formed by atomic layer deposition to provide the ternary metal conductor with a composition engineered to provide a desired thereshold voltage.

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— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

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